# FDA20N50 / FDA20N50_F109
# 500V N-Channel MOSFET

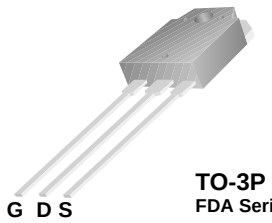
## Features

- 22A, 500V, $R_{DS(on)}$ = 0.23Ω @$V_{GS}$ = 10 V
- Low gate charge ( typical 45.6 nC)
- Low $C_{rss}$ ( typical 27 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

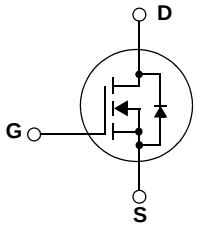
## Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies and active power factor correction.




**TO-3P**
**FDA Series**




## Absolute Maximum Ratings

| Symbol | Parameter | FDA20N50 | Unit |
|---|---|---|---|
| $V_{DSS}$ | Drain-Source Voltage | 500 | V |
| $I_D$ | Drain Current - Continuous ($T_C$ = 25°C)<br>- Continuous ($T_C$ = 100°C) | 22<br>13.2 | A<br>A |
| $I_{DM}$ | Drain Current - Pulsed (Note 1) | 88 | A |
| $V_{GSS}$ | Gate-Source voltage | ± 30 | V |
| $E_{AS}$ | Single Pulsed Avalanche Energy (Note 2) | 1110 | mJ |
| $I_{AR}$ | Avalanche Current (Note 1) | 22 | A |
| $E_{AR}$ | Repetitive Avalanche Energy (Note 1) | 28.0 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (Note 3) | 4.5 | V/ns |
| $P_D$ | Power Dissipation ($T_C$ = 25°C)<br>- Derate above 25°C | 280<br>2.3 | W<br>W/°C |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature Range | -55 to +150 | °C |
| $T_L$ | Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds | 300 | °C |

* Drain current limited by maximum junction termperature.

## Thermal Characteristics

| Symbol | Parameter | Min. | Max. | Unit |
|---|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | -- | 0.44 | °C/W |
| $R_{\theta CS}$ | Thermal Resistance, Case-to-Sink | 0.24 | -- | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | -- | 40 | °C/W |

## Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|---|---|---|---|---|---|
| FDA20N50 | FDA20N50 | TO-3P | -- | -- | 30 |
| FDA20N50 | FDA20N50_F109 | TO-3PN | -- | -- | 30 |

## Electrical Characteristics $T_C$ = 25°C unless otherwise noted

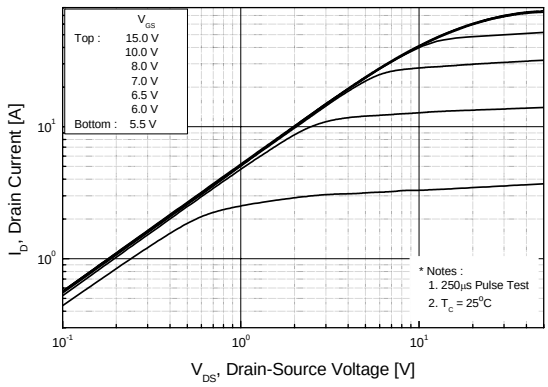
| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}$ = 0V, $I_D$ = 250μA, $T_J$ = 25°C | 500 | -- | -- | V |
| $\Delta BV_{DSS}$ / $\Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 250μA, Referenced to 25°C | -- | 0.50 | -- | V/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 500V, $V_{GS}$ = 0V<br>$V_{DS}$ = 400V, $T_C$ = 125°C | --<br>-- | --<br>-- | 1<br>10 | μA<br>μA |
| $I_{GSSF}$ | Gate-Body Leakage Current, Forward | $V_{GS}$ = 30V, $V_{DS}$ = 0V | -- | -- | 100 | nA |
| $I_{GSSR}$ | Gate-Body Leakage Current, Reverse | $V_{GS}$ = -30V, $V_{DS}$ = 0V | -- | -- | -100 | nA |
| **On Characteristics** | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 250μA | 3.0 | -- | 5.0 | V |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS}$ = 10V, $I_D$ = 11A | -- | 0.20 | 0.23 | Ω |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = 40V, $I_D$ = 11A (Note 4) | -- | 24.6 | -- | S |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 25V, $V_{GS}$ = 0V, f = 1.0MHz | -- | 2400 | 3120 | pF |
| $C_{oss}$ | Output Capacitance | | -- | 355 | 465 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | -- | 27 | -- | pF |
| **Switching Characteristics** | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD}$ = 250V, $I_D$ = 20A<br>$R_G$ = 25Ω (Note 4, 5) | -- | 95 | 200 | ns |
| $t_r$ | Turn-On Rise Time | | -- | 375 | 760 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | -- | 100 | 210 | ns |
| $t_f$ | Turn-Off Fall Time | | -- | 105 | 220 | ns |
| $Q_g$ | Total Gate Charge | $V_{DS}$ = 400V, $I_D$ = 20A<br>$V_{GS}$ = 10V (Note 4, 5) | -- | 45.6 | 59.5 | nC |
| $Q_{gs}$ | Gate-Source Charge | | -- | 14.8 | -- | nC |
| $Q_{gd}$ | Gate-Drain Charge | | -- | 21.6 | -- | nC |
| **Drain-Source Diode Characteristics and Maximum Ratings** | | | | | | |
| $I_S$ | Maximum Continuous Drain-Source Diode Forward Current | | -- | -- | 20 | A |
| $I_{SM}$ | Maximum Pulsed Drain-Source Diode Forward Current | | -- | -- | 80 | A |
| $V_{SD}$ | Drain-Source Diode Forward Voltage | $V_{GS}$ = 0V, $I_S$ = 22A | -- | -- | 1.4 | V |
| $t_{rr}$ | Reverse Recovery Time | $V_{GS}$ = 0V, $I_S$ = 20A<br>$dI_F/dt$ =100A/μs (Note 4) | -- | 507 | -- | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | -- | 7.20 | -- | μC |

**NOTES:**

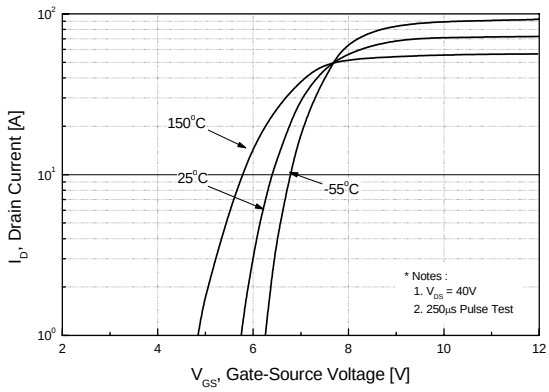
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 4.1mH, $I_{AS}$ = 22A, $V_{DD}$ = 50V, $R_G$ = 25Ω, Starting $T_J$ = 25°C
3. $I_{SD}$ ≤ 22A, di/dt ≤ 200A/μs, $V_{DD}$ ≤ $BV_{DSS}$, Starting $T_J$ = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

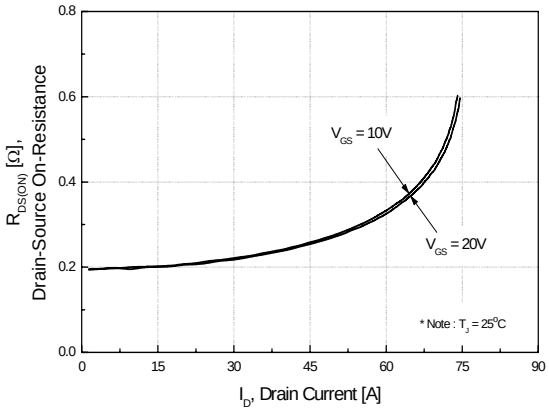
### Figure 1. On-Region Characteristics



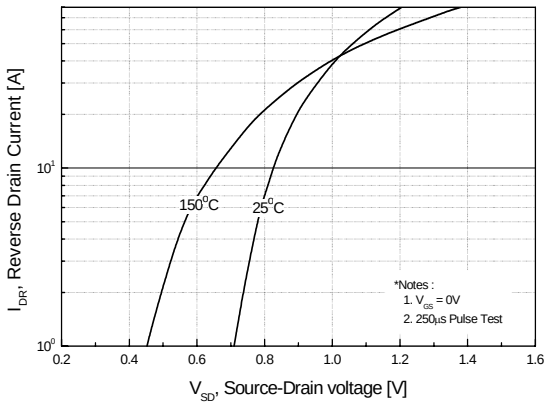

### Figure 2. Transfer Characteristics



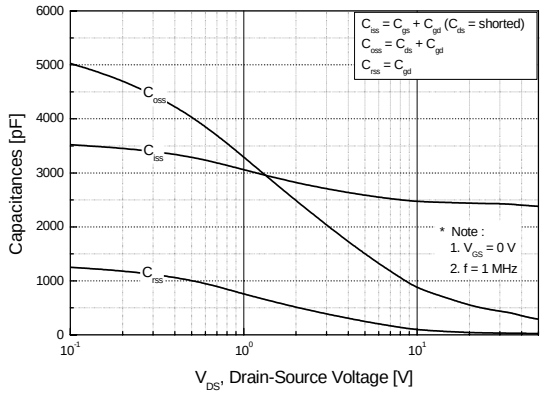

### Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage




### Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue




### Figure 5. Capacitance Characteristics




### Figure 6. Gate Charge Characteristics